### Accepted Manuscript

#### Research paper

Toxic gases molecules ( $NH_3$ ,  $SO_2$  and  $NO_2$ ) adsorption on GeSe monolayer with point defects engineering

Yuliang Mao, Linbo Long, Jianmei Yuan, Jianxin Zhong, Hongquan Zhao

PII:	S0009-2614(18)30539-6
DOI:	https://doi.org/10.1016/j.cplett.2018.06.061
Reference:	CPLETT 35760

To appear in: Chemical Physics Letters

Received Date:28 March 2018Revised Date:25 June 2018Accepted Date:29 June 2018



Please cite this article as: Y. Mao, L. Long, J. Yuan, J. Zhong, H. Zhao, Toxic gases molecules (NH<sub>3</sub>, SO<sub>2</sub> and NO<sub>2</sub>) adsorption on GeSe monolayer with point defects engineering, *Chemical Physics Letters* (2018), doi: https://doi.org/10.1016/j.cplett.2018.06.061

This is a PDF file of an unedited manuscript that has been accepted for publication. As a service to our customers we are providing this early version of the manuscript. The manuscript will undergo copyediting, typesetting, and review of the resulting proof before it is published in its final form. Please note that during the production process errors may be discovered which could affect the content, and all legal disclaimers that apply to the journal pertain.

# Toxic gases molecules (NH<sub>3</sub>, SO<sub>2</sub> and NO<sub>2</sub>) adsorption on GeSe monolayer with point defects engineering

Yuliang Mao<sup>†<sup>a</sup></sup>, Linbo Long<sup>a</sup>, Jianmei Yuan<sup>†<sup>b</sup></sup>, Jianxin Zhong<sup>a</sup>, Hongquan Zhao<sup>c</sup>

a. Hunan Key Laboratory for Micro–Nano Energy Materials and Devices, School of Physics and Optoelectronic, Xiangtan University, Hunan 411105, China.

b. Hunan Key Laboratory for Computation and Simulation in Science and Engineering, School of Mathematics and Computational Science, Xiangtan University, Hunan 411105, China.

c. Chongqing institute of Green and Intelligent Technology, Chinese Academy of Sciences, Chongqing 401120, China

<sup>†</sup> Corresponding authors, E-mail address: ylmao@xtu.edu.cn, yuanjm@xtu.edu.cn

#### Abstract

First-principles calculations are performed to study the structure, stability, density of states and work function of toxic gases (NH<sub>3</sub>, SO<sub>2</sub> and NO<sub>2</sub>) molecules adsorption on GeSe monolayer with point defect engineering, including Ge/Se mono-vacancy, anti-site defect, and P atom substituted defect. Our results on the adsorption energy, charge transfer and electron localization function show that the interaction between gas molecules and point defects in GeSe monolayer is sensitive, which causes significant modification to the electronic structure and work functions of GeSe monolayer.

Keywords: monolayer GeSe; point defect; first-principles; work function

Download English Version:

## https://daneshyari.com/en/article/7837659

Download Persian Version:

https://daneshyari.com/article/7837659

Daneshyari.com